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Docket No.: TCP-004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Confirmation No.

Kenji WATANABE et al

U.S. Patent Application No.: -----

Group Art Unit: -----

Filed: herewith

For:

A HIGHLY PURE HEXAGONAL BORON NITRIDE SINGLE CRYSTAL

CAPABLE OF EMITTING HIGH-LUMINANCE FAR ULTRAVIOLET LIGHT, A

METHOD FOR PRODUCING THE SAME, HIGH-LUMINANCE FAR

ULTRAVIOLET LIGHT EMITTING ELEMENT INLCUDING SAID SINGLE CRYSTAL, AND SOLID-STATE LASER AND SOLID STATE LIGHT EMITTING

APPARATUS UTILIZING THE ELEMENT

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed with the application and no certification or fee is required.

Please note this is a PCT application in the entry of the National Phase in the U.S. and copies of the references cited were transmitted by WIPO. Copies of the foreign search report and the references cited are attached for the Examiner's information. Acknowledgement and consideration of these documents are respectfully requested.

Respectfully submitted,

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Date: February 2, 2006

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

ATTY. DOCKET NO.
TCP-004

APPLICANT
Kenji WATANABE et al

FILING DATE

GROUP

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translat Yes	tion No
	2001-72499	03/21/2001	JP			abstract	
	6-219899	08/09/1994	JP			abstract	
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		. 194. 10081 * & V Z 11101*	nucleation of cubic boron nitr				i A. Se
	gradient method u	inder high pressure	e;" Journal of Crystal Growt	th, 2001, vol	. 222, pages	549-557.	
	FUKUNAGA et al and Related Mater	l; "Nucleation and rials, 2004, vol. 13,	growth of cubic boron nitrid pages 1709-1713.	le using a Ca	ı-B-N solven	t"; Diam	ond
			ence of the optical-absorption stry of Solids; 2002, vol. 63; p			hite-type	
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EXAMINER	<u>L,</u>		DATE CONSIDERE	ED			

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.